## Am27LV512

## Advanced Micro Devices

# 65,536 x 8-Bit CMOS Low Voltage, One Time Programmable Memory

#### **DISTINCTIVE CHARACTERISTICS**

- 3.3 V ± 0.3 V V<sub>CC</sub> read operation
- High performance at 3.3 V V<sub>CC</sub>
- 200 ns maximum access time
- Low power consumption
  - 90 μW maximum standby power
  - 25 µA maximum standby current
  - 54 mW maximum power at 5 MHz
  - 15 mA maximum current at 5 MHz
  - No data retention power
- Industry standard packaging
  - 32-pin PLCC
  - 32-pin Plastic DIP

- Program voltage 12.75 ± 0.25 V
- Latch-up protected to 100 mA from -1 V to Vcc +1 V
- Flashrite™ programming
  - 10 μs typical byte-program
  - Less than 1 second typical chip program
- Advanced CMOS memory technology
  - Low cost single transistor memory cell

#### **GENERAL DESCRIPTION**

The Am27LV512 device is a low voltage, low power, CMOS 64K x 8 One Time Programmable (OTP) non-volatile memory.

Maximum power consumption in standby mode is  $90\,\mu\text{W}$ . If the device is constantly accessed at 5 MHz, then maximum power consumption increases to 54 mW. These power ratings are significantly lower than typical EPROM devices. Since power consumption is proportional to voltage squared, 3.3 V devices typically consume at least 57% less power than 5.0 V devices.

The Am27LV512 typically draws 10 mA of current enabling 200 ns read operations. Typical power consumption under these conditions equals 33 mW. This "high performance", low voltage device is ideal for BIOS storage in portable computing applications and control code storage in portable digital cellular phone applications.

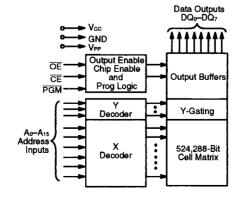
Low voltage CMOS designs require less operating power and hence dramatically increases the usable operating life of battery powered systems.

The Am27LV512 is packaged in standard 32-pin PLCC and Plastic DIP packages. It is designed to be programmed in standard EPROM programmers.

The highest degree of latch-up protection is achieved with AMD's proprietary non-epi process. Latch-up protection is provided for stresses up to 100 milliamps on address and data pins from –1 V to Vcc+1 V.

The Am27LV512 is byte programmable using 10  $\mu s$  programming pulses in accordance with AMD's Flashrite programming algorithm. The typical room temperature programming time of the Am27LV512 is less than one second.

## **BLOCK DIAGRAM**



08140-001A

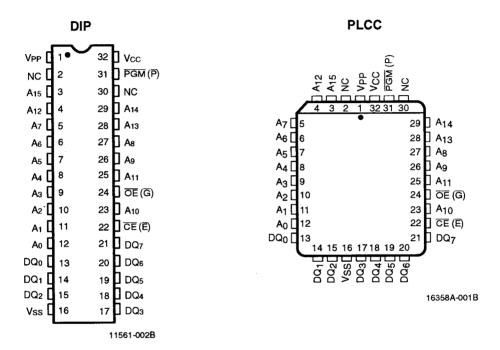
This document contains information on a product under development at Advanced Micro Devices, Inc. The Information is intended to help you evaluate this product. AMD reserves the right to change or discontinue work on this proposed product without notice.



## **PRODUCT SELECTOR GUIDE**

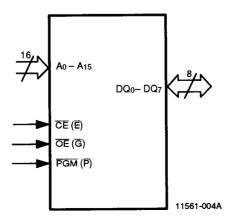
Family Part No.		Am27LV512	
Ordering Part No:			
±0.3 V Vcc Tolerance	-200	-250	-300
Max Access Time (ns)	200	250	300
CE (E) Access (ns)	200	250	300
OE (G) Access (ns)	75	100	100

## **CONNECTION DIAGRAMS**



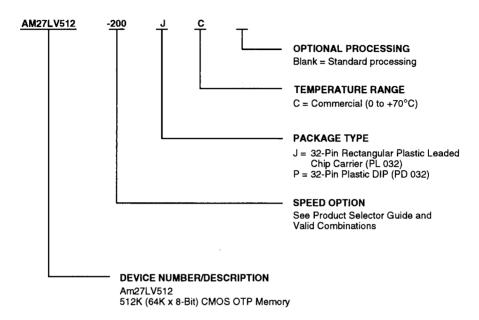
Note: Pin 1 is marked for orientation.

## LOGIC SYMBOL



## ORDERING INFORMATION Standard Products

AMD standard products are available in several packages and operating ranges. The ordering number (Valid Combination) is formed by a combination of these elements:



Valid Combinations					
Am27LV512-200					
Am27LV512-250	JC, PC				
Am27LV512-300					

#### **Valid Combinations**

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations and to check on newly released combinations.



#### PIN DESCRIPTION

#### $A_0 - A_{15}$

Address Inputs for memory locations.

#### DQ<sub>0</sub> - DQ<sub>7</sub>

Data Inputs during memory program cycles. Internal latches hold data during program cycles. Data Outputs during memory read cycles.

## CE (E)

The Chip Enable active low input activates the chip's control logic and input buffers. Chip Enable high will deselect the device and operates the chip in stand-by mode.

## OE (G)

The Output Enable active low input gates the outputs of the device through the data buffers during memory read cycles.

## PGM (P)

The Program Enable active low input controls the program function of the memory array.

#### V<sub>PF</sub>

Power supply for programming.

#### Vcc

Power supply for device operation. (Read:  $V_{CC} = 3.3 V \pm 0.3 V$ , Program:  $V_{CC} = 5.0 V \pm 10\%$ )

#### Vss

Ground

#### NC

No Connect-corresponding pin is not connected internally to the die.

### **BASIC PRINCIPLES**

The Am27LV512 supports programming operations using a fixed 12.75 ± .25 V power supply.

## **Read Only Memory**

Without high V<sub>PP</sub> voltage, the Am27LV512 functions as a read only memory and operates like a standard EPROM. The control inputs still manage traditional read, standby, output disable, and Auto select modes.

### **Programming**

These devices are programmable on standard PROM programmer equipment.

Please contact Advanced Micro Devices for PROM programmer information.

### **FUNCTIONAL DESCRIPTION**

### **Description Of User Modes**

Table 1. Am27LV512 User Bus Operations

	Operation		OE (G)	WE (W)	V <sub>PP</sub> (Note 1)	Ao	<b>A</b> 9	I/O
	Read	VIL	VIL	Х	VPPL	Ao	<b>A</b> 9	Dоит
	Standby	ViH	Х	Х	V <sub>PPL</sub>	X	Х	HIGH Z
Read-Only	Output Disable	VIL	ViH	ViH	VPPL	Х	Х	HIGH Z
1	Auto-select Manufacturer Code	VıL	VıL	ViH	VPPL	VıL	V <sub>ID</sub> (Note 2)	CODE (01H)
	Auto-select Device Code	VIL	ViL	Vıн	VPPL	V <sub>IH</sub>	V <sub>ID</sub> (Note 2)	CODE (26H)

#### Legend:

X = Don't care, where Don't Care is either  $V_{IL}$  or  $V_{IH}$  levels,  $V_{PPL} = V_{PP} < V_{CC} + 2 V$ , See DC Characteristics for voltage levels of  $V_{PPH}$ , 0 V < An < V<sub>CC</sub> + 2 V, (normal CMOS input levels, where n = 0 or 9).

#### Notes:

- VPPL may be grounded, connected with a resistor to ground, or ≤ VCC +2.0V. VPPH is the programming voltage specified for the device. Refer to the DC characteristics. When VPP = VPPL, memory contents can be read but not written.
- 2.  $11.5 \le \text{ViD} \le 13.0 \text{ V}$ ,  $\text{Vcc} = 5.0 \text{ V} \pm 10\%$ .

#### **READ ONLY MODE**

 $V_{cc}$  = 3.3 V  $\pm$  0.3 V

#### Read

The Am27LV512 functions as a read only memory. The Am27LV512 has two control functions. Both must be satisfied in order to output data.  $\overline{\text{CE}}$  controls power to the device. This pin should be used for specific device selection.  $\overline{\text{OE}}$  controls the device outputs and should be used to gate data to the output pins if a device is selected.

Address access time  $t_{ACC}$  is equal to the delay from stable addresses to valid output data. The chip enable access time  $t_{CE}$  is the delay from stable addresses and stable  $\overline{CE}$  to valid data at the output pins. The output enable access time is the delay from the falling edge of  $\overline{OE}$  to valid data at the output pins (assuming the addresses have been stable at least  $t_{ACC} - t_{OE}$ ).

#### **Standby Mode**

The Am27LV512 has one standby mode. The CMOS standby mode ( $\overline{\text{CE}}$  input held at V<sub>CC</sub>  $\pm$  0.5 V), consumes less than 25  $\mu$ A of current. When in the standby mode the outputs are in a high impedance state, independent of the  $\overline{\text{OE}}$  input.

If the device is deselected during programming, or program verification, the device will draw active current until the operation is terminated.

#### **Output Disable**

Output from the device is disabled when  $\overline{OE}$  is at a logic high level. When disabled, output pins are in a high impedance state.

#### **Auto Select**

The Am27LV512 can be programmed in a standard PROM programmer.

The Auto select mode allows the reading out of a binary code from the device that will identify its manufacturer and type. This mode is intended for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm.

#### Programming In A PROM Programmer

To activate this mode, the programming equipment must force  $V_{\rm ID}$  (11.5 V to 13.0 V) on address  $A_9$ . Two identifier bytes may then be sequenced from the device outputs by toggling address  $A_0$  from  $V_{\rm IL}$  to  $V_{\rm IH}$ . All other address lines must be held at  $V_{\rm IL}$ , and  $V_{\rm PP}$  must be less than or equal to  $V_{\rm CC}+2.0$  V while using this Auto select mode. Byte 0 ( $A_0=V_{\rm IL}$ ) represents the manufacturer code and byte 1 ( $A_0=V_{\rm IH}$ ) the device identifier code. For the Am27LV512 these two bytes are given in the table below. All identifiers for manufacturer and device codes will exhibit odd parity with the MSB (DQ7) defined as the parity bit.

Table 2. Am27LV512 Auto Select Code

Туре	Ao	Code (HEX)	DQ <sub>7</sub>	DQ <sub>6</sub>	DQ₅	DQ4	DQ₃	DQ <sub>2</sub>	DQ <sub>1</sub>	DQ₀
Manufacturer Code	٧L	01	0	0	0	0	0	0	0	1
Device Code	ViH	26	0	0	1	0	0	1	1	0



## **ABSOLUTE MAXIMUM RATINGS**

	ge Temperature stic Packages – 65°C to +125°C
	ent Temperature n Power Applied – 55°C to + 125°C
Volta	ge with Respect To Ground All pins
	ept A <sub>9</sub> and V <sub>PP</sub> (Note 1) 2.0 V to 7.0 V
Vcc (	Note 1) – 2.0 V to 7.0 V
A9 (N	ote 2)
V <sub>PP</sub> (	Note 2)
	ut Short Circuit Current (Note 3) 200 mA

### Notes:

- Minimum DC voltage on input or I/O pins is -0.5 V. During voltage transitions, inputs may overshoot Vss to -2.0 V for periods of up to 20 ns. Maximum DC voltage on output and I/O pins is Vcc + 0.5 V. During voltage transitions, outputs may overshoot to Vcc + 2.0 V for periods up to 20 ns.
- Minimum DC input voltage on A9 and VPP pins is -0.5V.
   During voltage transitions, A9 and VPP may overshoot Vss to -2.0 V for periods of up to 20 ns. Maximum DC input voltage on A9 and VPP is +13.5 V which may overshoot to 14.0 V for periods up to 20 ns.
- No more than one output shorted at a time. Duration of the short circuit should not be greater than one second.

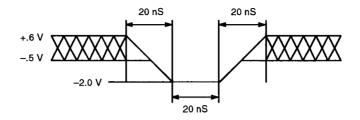
Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure of the device to absolute maximum rating conditions for extended periods may affect device reliability.

## **OPERATING RANGES**

Commercial (C) Devices Case Temperature (Tc) 0°C to +70°C
Vcc Supply Voltage Vcc for Am27LV512+3.0 V to +3.6 V
V <sub>PP</sub> Supply Voltage
Program and Verify +12.5 V to +13 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

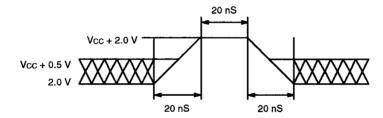
# MAXIMUM OVERSHOOT Maximum Negative Input Overshoot



11561-009B

## **Maximum Negative Overshoot Waveform**

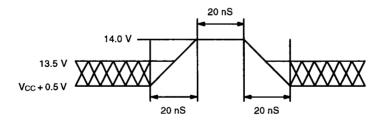
## **Maximum Positive Input Overshoot**



11561-010A

#### **Maximum Positive Overshoot Waveform**

## Maximum V<sub>PP</sub> Overshoot



11561-011A

**Maximum VPP Overshoot Waveform** 



## DC CHARACTERISTICS-CMOS COMPATIBLE

Parameter Symbol	Parameter Description	Test Conditions	Min.	Max.	Unit
lu	Input Leakage Current	V <sub>CC</sub> = V <sub>CC</sub> Max., V <sub>IN</sub> = V <sub>CC</sub> or V <sub>SS</sub>		+ 1.0	μΑ
lLO	Output Leakage Current	Vcc = Vcc Max., Vout = Vcc or Vss		+ 1.0	μΑ
lccs	Vcc Standby Current	V <sub>CC</sub> = V <sub>CC</sub> Max. CE = V <sub>CC</sub> ± 0.3 V		25	μΑ
lcc1	Vcc Active Read Current	V <sub>CC</sub> = V <sub>CC</sub> Max., $\overline{CE}$ = V <sub>IL</sub> , $\overline{OE}$ = V <sub>IH</sub> l <sub>OUT</sub> = 0 mA, at 5 MHz		15	mA
lcc2	Vcc Programming Current	CE = V <sub>IL</sub> Programming in Progress		30	mA
IPPS	V <sub>PP</sub> Standby Current	V <sub>PP</sub> = V <sub>PPL</sub>		+ 1.0	μΑ
VIL	Input Low Voltage		-0.5	0.6	V
ViH	Input High Voltage		2.0	V <sub>CC</sub> + 0.5	٧
Vol	Output Low Voltage	IoL = 1 mA Vcc = Vcc Min.		0.3	٧
Vон	Output High Voltage	I <sub>OH</sub> = -100 μA, V <sub>CC</sub> = V <sub>CC</sub> Min.	V <sub>CC</sub> -0.3		V
V <sub>ID</sub>	A <sub>9</sub> Auto Select Voltage	Ag = VID	11.5	13.0	٧
lıD	Ag Auto Select Current	A <sub>9</sub> = V <sub>ID</sub> Max. V <sub>CC</sub> = V <sub>CC</sub> Max.		35	μΑ
V <sub>PPL</sub>	V <sub>PP</sub> during Read-Only Operations		0.0	Vcc + 2.0	٧
V <sub>РРН</sub>	V <sub>PP</sub> during Read/Write Operations		12.5	13.0	٧

## Notes:

- 1. Caution: the Am27LV512 must not be removed from (or inserted into) a socket when Vcc or Vpp is applied.
- 2.  $I_{CC1}$  is tested with  $\overline{OE} = V_{IH}$  to simulate open outputs.
- 3. Maximum active power usage is the sum of lcc and lpp.

#### PIN CAPACITANCE

Parameter Symbol	Parameter Description	Test Conditions	Тур.	Max.	Unit
Cin	Input Capacitance	V <sub>IN</sub> = 0	8	10	рF
Соит	Output Capacitance	V <sub>OUT</sub> = 0	8	12	рF
C <sub>IN2</sub>	V <sub>PP</sub> Input Capacitance	V <sub>PP</sub> = 0	8	12	pF

#### Notes:

- 1. Sampled, not 100% tested.
- 2. Test conditions TA = 25°C, f = 1.0 MHz.

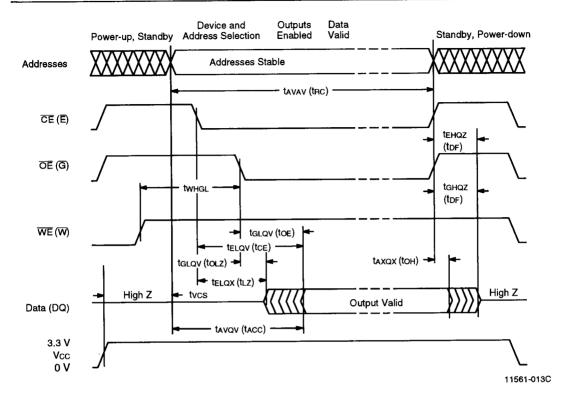
# SWITCHING CHARACTERISTICS over operating range unless otherwise specified AC CHARACTERISTICS-Read Only Operation (Notes 1– 2)

Parameter Symbols				Am27LV512			
JEDEC	Standard	Parameter Description		-200	-250	-300	Unit
tavav	tac	Read Cycle Time	Min. Max.	200	250	300	ns
tELQV	tce	Chip Enable Access Time	Min. Max.	200	250	300	ns
tavqv	tacc	Address Access Time	Min. Max.	200	250	300	ns
tGLQV	toe	Output Enable Access Time	Min. Max.	75	100	100	ns
tELQX	tız	Chip Enable to Output in Low Z	Min. Max.	0	0	0	ns
tenoz	t <sub>DF</sub>	Chip Disable to Output in High Z	Min. Max.	35	35	35	ns
tgLax	touz	Output Enable to Output in Low Z	Min. Max.	0	0	0	ns
tвноz	tor	Output Disable to Output in High Z	Min. Max.	35	35	35	ns
taxox	tон	Output Hold from first of Address, CE, or OE Change	Min. Max.	0	0	0	ns
tvcs		V <sub>CC</sub> Set-up Time to Valid Read	Min. Max.	50	50	50	μs

#### Notes:

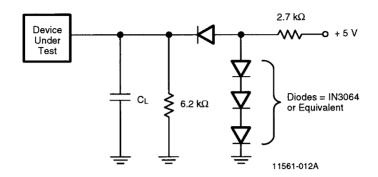
- Output Load: 1 TTL gate and C<sub>L</sub> = 100 pF, Input Rise and Fall Times: ≤ 10 ns, Input Pulse levels: 0.45 to 2.4 V, Timing Measurement Reference Level - Inputs: 0.6 V and 2 V Outputs: 1.5 V
- 2. tvcs is guaranteed by design not tested.





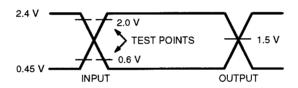
**AC Waveforms for Read Operations** 

## **SWITCHING TEST CIRCUIT**



C<sub>L</sub> = 100 pF including jig capacitance

## **SWITCHING TEST WAVEFORMS**



All Devices

AC Testing: Inputs are driven at 2.4 V for a logic "1" and 0.45 V for a logic "0". Input pulse rise and fall times are  $\leq$  10 ns.

16357A-002B



## **ERASE AND PROGRAMMING PERFORMANCE**

		Limits			
Parameter	Min.	Тур.	Max.	Unit	Comments
Chip Programming Time		1 (Note 1)	12	s	Excludes system-level overhead

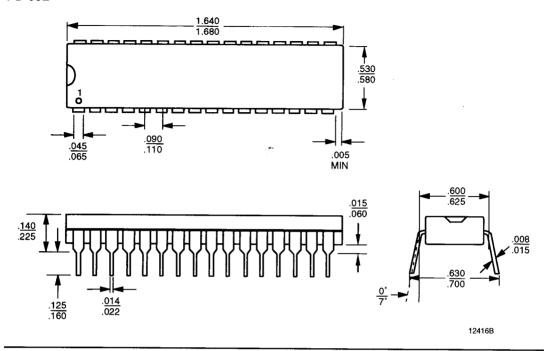
## Note:

1. 25°C, 12.75 V VPP

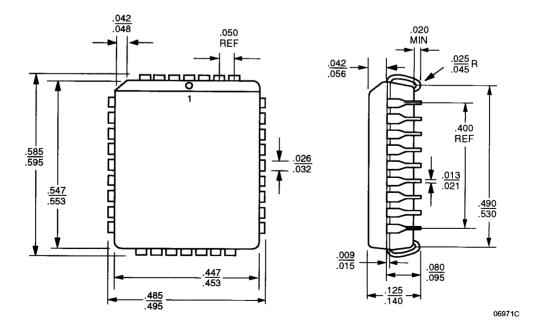
## LATCHUP CHARACTERISTICS

	Min.	Max.
Input Voltage with respect to Vss on all pins except I/O pins		
(Including A <sub>9</sub> and V <sub>PP</sub> )	−1.0 V	13.5 V
Input Voltage with respect to Vss on all pins I/O pins	-1.0 V	Vcc + 1.0 V
Current	-100 mA	+100 mA
Includes all pins except Vcc. Test conditions: Vcc = 5.0 V, one pin at a	time.	

## PHYSICAL DIMENSIONS\* PD 032



PL 032



\*For reference only. All dimensions are measured in inches, unless otherwise noted. BSC is an ANSI standard for Basic Space Centering.